

## CLAIMS

1. A semiconductor device comprising:  
a support which is a sheet comprising a ferromagnetic material;  
a binding material adjacent to the sheet comprising the ferromagnetic material;  
5 and  
an element on an insulating film adjacent to the binding material.
2. A semiconductor device according to claim 1, wherein the element is a thin film transistor, a light-emitting element having a layer containing an organic compound,  
10 an element having liquid crystal, a memory element, a thin film diode, a photoelectric transducer comprising PIN junctions of silicon, or a silicon resistance element.
3. A semiconductor device according to claim 1 or claim 2, wherein the sheet comprising the ferromagnetic material is formed by mixing soft magnetic powder and  
15 synthetic resin, then magnetized.
4. A semiconductor device comprising:  
a support which is a binding material;  
a protective film on the binding material;  
20 a middle processing component comprising a control section and an operation section, and a memory unit on an insulating film adjacent to the binding material; and  
the middle processing component includes a thin film transistor of n-channel type and a thin film transistor of p-channel type.
- 25 5. A semiconductor device according to any one of claims 1 through 4, wherein the semiconductor device is an authentication card, a video camera, a digital camera, a goggle type display, a car navigation system, a personal computer, or a mobile information terminal.
- 30 6. A manufacturing method of a semiconductor device comprising the

following steps:

a first step of forming a layer to be peeled including a semiconductor element on a first substrate;

5 a second step of binding a second substrate provided with an etching stopper layer onto the later to be peeled with a binding material; and

a third step of removing only the second substrate by etching or polishing.

7. A manufacturing method of a semiconductor device comprising the following steps:

10 a first step of forming a first etching stopper layer on a first substrate;

a second step of forming a layer to be peeled including a semiconductor element on the first etching stopper layer;

a third step of binding a second substrate provided with a second etching stopper layer onto the layer to be peeled with a binding material; and

15 a fourth step of removing at least one of the first substrate or the second substrate by etching or polishing.

8. A manufacturing method of a semiconductor device according to claim 6 or claim 7, wherein the etching stopper layer is SrO, SnO<sub>2</sub>, fluoropolymer, monolayer of W, or these lamination layer.

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9. A manufacturing method of a semiconductor device comprising the following steps:

25 a first step of forming a layer to be peeled including a semiconductor element on a first substrate;

a second step of applying a film containing organic resin which dissolves to solvent on the layer to be peeled;

a third step of adhering a second substrate on the film containing the organic resin with a first double-stick tape, and sandwiching the layer to be peeled and the film containing the organic resin between the first substrate and the second substrate;

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a fourth step of adhering a third substrate to the first substrate with a second double-stick tape;

a fifth step of separating the first substrate on which the third substrate is adhered from the layer to be peeled by a physical means;

5 a sixth step of adhering a sheet comprising a ferromagnetic material to the layer to be peeled with a first binding material, and sandwiching the layer to be peeled between the second substrate and the sheet comprising the ferromagnetic material;

a seventh step of separating the layer to be peeled and the first double-stick tape from the second substrate;

10 an eighth step of separating the layer to be peeled from the first double-stick tape; and

a ninth step of removing the film containing the organic resin with solvent.

15 10. A manufacturing method of a semiconductor device comprising the following steps:

a first step of forming a layer to be peeled including a semiconductor element on a first substrate;

a second step of applying a film containing organic resin which dissolves to solvent on the layer to be peeled;

20 a third step of adhering a second substrate on the film containing the organic resin with a first double-stick tape, and sandwiching the layer to be peeled and the film containing the organic resin between the first substrate and the second substrate;

a fourth step of adhering a third substrate to the first substrate with a second double-stick tape;

25 a fifth step of separating the first substrate on which the third substrate is adhered from the layer to be peeled by a physical means;

a sixth step of adhering a sheet comprising a ferromagnetic material to the layer to be peeled with a first binding material, and sandwiching the layer to be peeled between the second substrate and the sheet comprising the ferromagnetic material;

30 a seventh step of separating the layer to be peeled and the first double-stick

tape from the second substrate;

an eighth step of separating the layer to be peeled from the first double-stick tape;

a ninth step of removing the film containing the organic resin with solvent; and

5 a tenth step of adhering a seal substrate to the layer to be peeled with a second binding material, and sandwiching the layer to be peeled between the sheet comprising the ferromagnetic material and the seal substrate.

11. A manufacturing method of a semiconductor device comprising the  
10 following steps:

a first step of forming a layer to be peeled including TFT on a first substrate;

a second step of applying a film containing organic resin which dissolves to solvent on the layer to be peeled;

15 a third step of adhering a second substrate on the film containing the organic resin with a first double-stick tape, and sandwiching the layer to be peeled and the film containing the organic resin between the first substrate and the second substrate;

a fourth step of adhering a third substrate to the first substrate with a second double-stick tape;

20 a fifth step of separating the first substrate on which the third substrate is adhered from the layer to be peeled by a physical means;

a sixth step of adhering a fourth substrate to the layer to be peeled with a first binding material, and sandwiching the layer to be peeled between the second substrate and the fourth substrate;

25 a seventh step of separating the layer to be peeled and the first double-stick tape from the second substrate;

an eighth step of separating the layer to be peeled from the first double-stick tape;

a ninth step of removing the film containing the organic resin with solvent;

30 a tenth step of forming a light-emitting element containing an organic compound on the layer to be peeled; and

an eleventh step of pasting a sheet comprising a ferromagnetic material which seals the light-emitting element with a second binding material, and sandwiching the layer to be peeled between the fourth substrate and the sheet comprising the ferromagnetic material.

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12. A manufacturing method of a semiconductor device according to any one of claims 9 through 11, wherein the solvent is water or alcohol.

10 13. A manufacturing method of a semiconductor device according to any one of claims 9 through 12, wherein the adhesion of the layer to be peeled and the sheet comprising the ferromagnetic material or the fourth substrate is higher than the adhesion of the first double-stick tape and the second substrate in the seventh process.

15 14. A manufacturing method of a semiconductor device according to any one of claims 9 through 13, wherein the first substrate is a glass substrate, the second substrate and the third substrate is a ceramic substrate or a metal substrate, and the fourth substrate is a plastic substrate.

20 15. A manufacturing method of a semiconductor device according to any one of claims 9 through 13, wherein the fourth substrate is a plastic film which a protective film is formed on the surface.

25 16. A manufacturing method of a semiconductor device according to any one of claims 9 through 15, wherein the layer to be peeled includes a thin film transistor, a light-emitting element having a layer containing an organic compound, an element having liquid crystal, a memory element, a thin film diode, a photoelectric transducer comprising PIN junctions of silicon, or a silicon resistance element.